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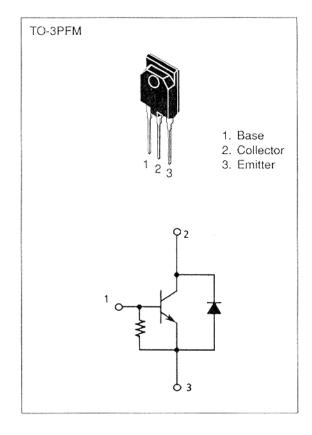
Silicon NPN Triple Diffused Character Display Horizontal Deflection Output

Feature

- High breakdown voltage V_{CES} = 1500 V
- · Built-in dampen diode type
- · Isolated package; TO-3PFM

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to emitter voltage	V_{CES}	1500	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	l _C	6	Α
Collector peak current	i _{C(peak)}	7	Α
Collector surge current	i _{C(surge)}	16	Α
Collector power dissipation	P _C *1	50	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C
C to E diode forward current	ID	7	Α



Note: 1. Value at $T_C = 25$ °C.

Electrical Characteristics (Ta = 25°C)

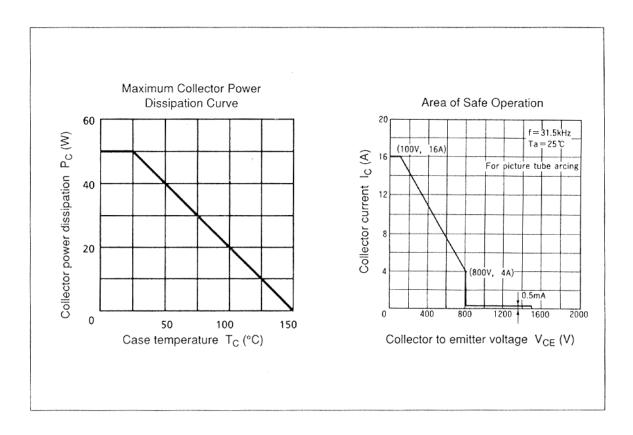
Item	Symbol	Min	Тур	Max	Unit	Test condition
Emitter to base breakdown voltage	V _{(BR)EBO}	6			٧	I _E = 400 mA, I _C = 0
Collector cutoff current	I _{CES}		and the same of th	500	μΑ	V _{CE} = 1500 V, R _{BE} = 0
DC current transfer ratio	h _{FE}	******		25		$V_{CE} = 5 \text{ V, } I_{C} = 1 \text{ A}$
Collector to emitter saturation voltage	V _{CE(sat)}		annua .	2.0	٧	I _C = 5 A, I _B = 1.25 A
Base to emitter saturation voltage	V _{BE(sat)}			1.5	٧	I _C = 5 A, I _B = 1.25 A
C to E diode forward voltage	V _{ECF}	and the sale		2.0	V	I _F = 6 A

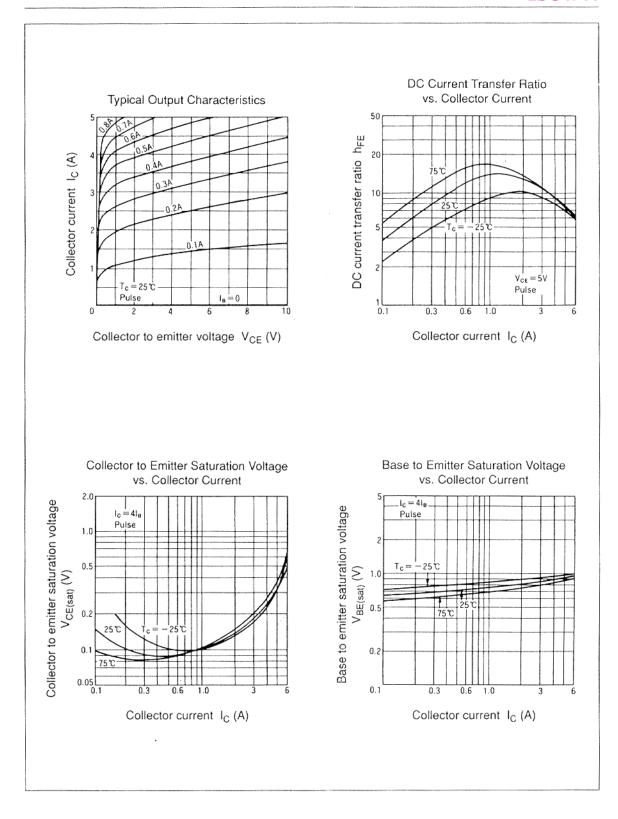
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Electrical Characteristics (Ta = 25°C) (cont)

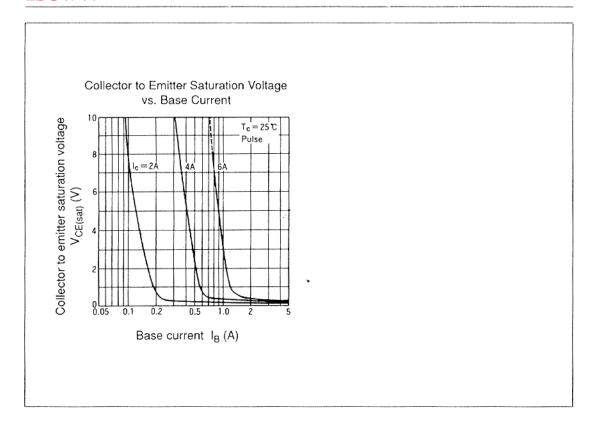
Item	Symbol	Min	Тур	Max	Unit	Test condition
Fall time	t _f		-	0.4	μs	$I_{CP} = 5 \text{ A}, I_{B1} = 1 \text{ A}$ $I_{B2} = -2 \text{ A}$





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